

Homework 1  
Date assigned: 09/15/2015  
Date due: 09/22/2015 (MIDNIGHT)

**Problem 1**

Consider a wafer of radius  $w_r$  as shown in Figure 1. Assume square dies on the wafer with side dimension  $d_e$ .

- a. Calculate the number of useful dies (“physically intact”) on the wafer in terms of  $w_r$  and  $d_e$ .
- b. What is the minimum ratio  $w_r/d_e$  for which at least one useful die is obtained.
- c. Plot the number of useful dies as a function of the ratio  $w_r/d_e$ . Make sure that the limits of  $w_r/d_e$  are correct as obtained in answer (b) above.
- d. Assume that the wafer has a defect density of  $D_d$  per unit area. Calculate the wafer yield,  $Y$ .  
Note that the wafer yield is defined as  $Y = (\text{no. of physically intact dies on the wafer}) \times (\text{die yield})$ . To compute  $Y$ , you have to use the results from part (a) above.

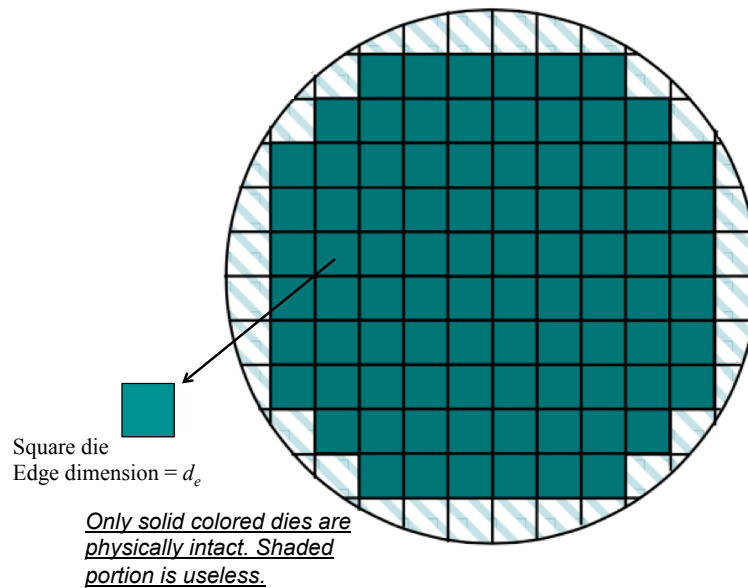


Figure 1: The wafer radius is  $w_r$ . Shaded dies are useful. To find answer to part (a), calculate how much area is wasted in the shaded portion.

## Problem 2

Consider the  $I_D$ - $V_d$  characteristics of the transistor for  $V_{gs} > V_T$ . That is, the transistor is in ON condition.

- a. Compute the resistance of the transistor as  $(\partial I_D / \partial V_d)^{-1}$  for linear and saturation regimes of transport.
- b. Qualitatively plot the resistance as a function of  $V_{ds}$  and  $V_{gs}$  on two separate plots.

Your answer must be presented in a tabular format as below.

<b>Linear operation</b>	<b>Saturation operation</b>
Transistor resistance = <Your answer>	Transistor resistance = <Your answer>
Qualitative plot of transistor resistance versus $V_{ds}$ .	Qualitative plot of transistor resistance versus $V_{ds}$ .
Qualitative plot of transistor resistance versus $V_{gs}$ .	Qualitative plot of transistor resistance versus $V_{gs}$ .

## Problem 3

Consider the  $I_D$ - $V_g$  characteristics of the transistor.

- a. Derive the transistor trans-conductance  $g_m = \partial I_D / \partial V_g$  for  $V_{gs} < V_T$ . Recall: for  $V_{gs} < V_T$ , transistor current varies exponentially with  $V_{gs} - V_T$ . Note that the dependence of  $I_D$  on  $V_d$  is very weak for  $V_{gs} < V_T$ .
- b. Derive the transistor trans-conductance for  $V_{gs} > V_T$ . Recall: for  $V_{gs} > V_T$ , transistor is ON. But the current  $I_D$  depends on whether the device is in linear or saturation modes of transport. For this part, you need to derive the results for both linear and saturation regimes.

Your answer must be presented in a tabular format as below.

<b><math>V_{gs} &lt; V_T</math> (OFF conditions) and assume <math>V_{ds} \gg k_B T / q</math></b>
Trans-conductance = <Your answer>
Qualitative plot of trans-conductance versus $V_{gs}$ .

<b><math>V_{gs} &gt; V_T</math> (ON conditions)</b>	
<b>Linear operation</b>	<b>Saturation operation</b>
Trans-conductance = <Your answer>	Trans-conductance = <Your answer>
Qualitative plot of transistor resistance versus $V_{ds}$ .	Qualitative plot of transistor resistance versus $V_{ds}$ .
Qualitative plot of transistor resistance versus $V_{gs}$ .	Qualitative plot of transistor resistance versus $V_{gs}$ .